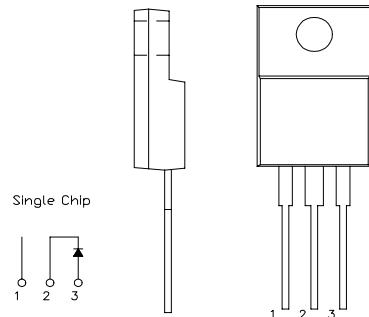


# SBD Type : FSQ05A03LB

OUTLINE DRAWING

## FEATURES

- \*Similar to TO-220AB Case
- \*Fully Molded Isolation
- \*Extremely Low Forward Voltage Drop
- \*Low Power Loss, High Efficiency
- \*High Surge Capability
- \* $T_j=150\text{ }^{\circ}\text{C}$  operation



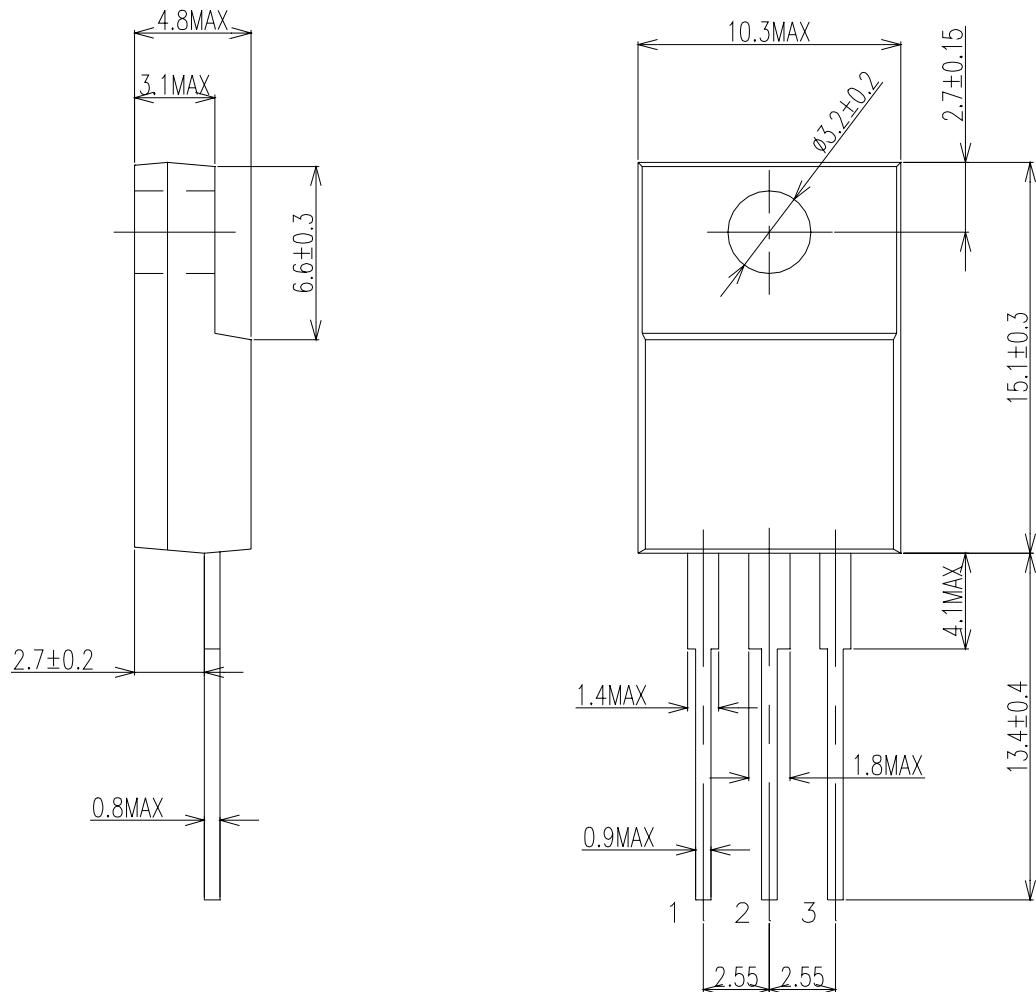
## Maximum Ratings

Approx Net Weight: 1.75g

Rating	Symbol	FSQ05A03LB			Unit		
Repetitive Peak Reverse Voltage	$V_{RRM}$	30			V		
Repetitive Peak Surge Reverse Voltage	$V_{RRSM}$	35(pulse width $\leq 1\mu\text{s}$ duty $\leq 1/50$ )			V		
Average Rectified Output Current	$I_o$	5	$T_c=122\text{ }^{\circ}\text{C}$	50 Hz half Sine Wave Resistive Load	A		
RMS Forward Current	$I_{F(RMS)}$	7.85			A		
Surge Forward Current	$I_{FSM}$	120	50Hz Half Sine Wave ,1cycle Non-repetitive		A		
Operating JunctionTemperature Range	$T_{jw}$	-40 to +150			$^{\circ}\text{C}$		
Storage Temperature Range	$T_{stg}$	-40 to +150			$^{\circ}\text{C}$		
Mounting torque	$F_{tor}$	recommended torque = 0.5			N•m		

## Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	$I_{RM}$	$T_j= 25\text{ }^{\circ}\text{C}$ , $V_{RM}= V_{RRM}$	-	-	5	mA
Peak Forward Voltage	$V_{FM}$	$T_j= 25\text{ }^{\circ}\text{C}$ , $I_{FM}= 5 \text{ A}$	-	-	0.47	V
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	-	-	5	$^{\circ}\text{C}/\text{W}$
	$R_{th(c-f)}$	Cace to Fin	-	-	1.5	$^{\circ}\text{C}/\text{W}$

**FSQ05A03LB OUTLINE DRAWING (Dimention in mm)**


Single Chip

